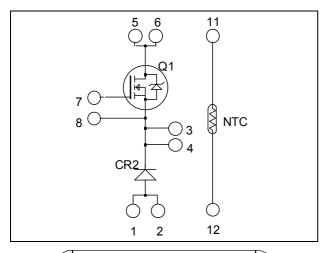
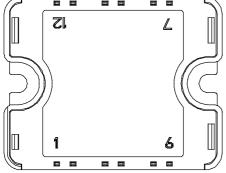


Buck chopper MOSFET Power Module

$$\begin{split} V_{DSS} &= 1000V \\ R_{DSon} &= 330 m \Omega \text{ typ } \text{ } \text{ } \text{ } \text{Tj} = 25^{\circ}\text{C} \\ I_D &= 23 \text{A} \text{ } \text{ } \text{ } \text{ } \text{Tc} = 25^{\circ}\text{C} \end{split}$$





Pins 1/2; 3/4; 5/6 must be shorted together

Application

- AC and DC motor control
- Switched Mode Power Supplies

Features

- Power MOS 8TM MOSFETs
 - Low R_{DSon}
 - Low input and Miller capacitance
 - Low gate charge
 - Avalanche energy rated
 - Very rugged
- Very low stray inductance
- Internal thermistor for temperature monitoring
- High level of integration

Benefits

- Outstanding performance at high frequency operation
- Direct mounting to heatsink (isolated package)
- Low junction to case thermal resistance
- Solderable terminals both for power and signal for easy PCB mounting
- Low profile
- RoHS Compliant

Absolute maximum ratings

Symbol	Parameter		Max ratings	Unit
$V_{ m DSS}$	Drain - Source Breakdown Voltage		1000	V
т	Continuous Drain Current	$T_c = 25^{\circ}C$	23	
I_{D}	Continuous Diani Current	$T_c = 80$ °C	17	A
I_{DM}	Pulsed Drain current		140	
V_{GS}	Gate - Source Voltage		±30	V
R _{DSon}	Drain - Source ON Resistance		396	mΩ
P_{D}	Maximum Power Dissipation	$T_c = 25^{\circ}C$	390	W
I_{AR}	Avalanche current (repetitive and non repetitive)		18	A

CAUTION: These Devices are sensitive to Electrostatic Discharge. Proper Handling Procedures Should Be Followed. See application note APT0502 on www.microsemi.com



All ratings @ $T_j = 25$ °C unless otherwise specified

Electrical Characteristics

Symbol	Characteristic	Test Conditions		Min	Тур	Max	Unit
T	Zero Gate Voltage Drain Current	$V_{DS} = 1000V$	$T_j = 25$ °C			100	μA
I_{DSS}		$V_{GS} = 0V$	$T_j = 125$ °C			500	μΑ
R _{DS(on)}	Drain – Source on Resistance	$V_{GS} = 10V, I_D = 18A$		330	396	mΩ	
$V_{GS(th)}$	Gate Threshold Voltage	$V_{GS} = V_{DS}, I_{D} = 2.5 m$	3	4	5	V	
I_{GSS}	Gate – Source Leakage Current	$V_{GS} = \pm 30 \text{ V}$				±100	nA

Dynamic Characteristics

Symbol	Characteristic	Test Conditions	Min	Typ	Max	Unit
C_{iss}	Input Capacitance	$V_{GS} = 0V$		7868		
C_{oss}	Output Capacitance	$V_{\rm DS} = 25V$		825		pF
C_{rss}	Reverse Transfer Capacitance	f = 1MHz		104		
Q_{g}	Total gate Charge	$V_{GS} = 10V$		305		
Q_{gs}	Gate – Source Charge	$V_{Bus} = 500V$		55		nC
Q_{gd}	Gate – Drain Charge	$I_{D} = 18A$		145		
$T_{d(on)}$	Turn-on Delay Time	Resistive switching @ 25°C		44		
$T_{\rm r}$	Rise Time	$\begin{split} V_{GS} &= 15 V \\ V_{Bus} &= 667 V \\ I_D &= 18 A \\ R_G &= 2.2 \Omega \end{split}$		40		
$T_{d(off)}$	Turn-off Delay Time			150		ns
T_{f}	Fall Time			38		

Chopper diode ratings and characteristics

Symbol	Characteristic	Test Conditions	Min	Typ	Max	Unit	
V_{RRM}	Maximum Peak Repetitive Reverse Voltage			1200			V
I_{RM}	Maximum Reverse Leakage Current	V _R =1200V	$T_i = 25^{\circ}C$ $T_i = 125^{\circ}C$			100 500	μΑ
I_F	DC Forward Current		$Tc = 80^{\circ}C$		30		A
		$I_F = 30A$			2.6	3.1	
V_{F}	Diode Forward Voltage	$I_F = 60A$		3.2		V	
		$I_F = 30A$	$T_{i} = 125^{\circ}C$		1.8		
+	Reverse Recovery Time	$I_F = 30A$ $V_R = 800V$	$T_j = 25$ °C		300		ns
t_{rr}	Reverse Recovery Time		$T_j = 125$ °C		380		115
Qrr	Reverse Recovery Charge	$di/dt = 200A/\mu s$	$T_j = 25$ °C		360		nC
			$T_{j} = 125^{\circ}C$		1700		пС

Thermal and package characteristics

Symbol	Characteristic				Min	Тур	Max	Unit
R_{thJC}	Junction to Case Thermal Resistance		Trans	istor			0.32	°C/W
κ_{thJC}			Diode)			1.2	C/ VV
V_{ISOL}	RMS Isolation Voltage, any terminal to case t = 1 min, 50/60Hz			4000			V	
T_{J}	Operating junction temperature range			-40		150		
T_{STG}	Storage Temperature Range				-40		125	°C
$T_{\rm C}$	Operating Case Temperature						100	
Torque	Mounting torque	ing torque To heatsink M4		2		3	N.m	
Wt	Package Weight		•			•	80	g



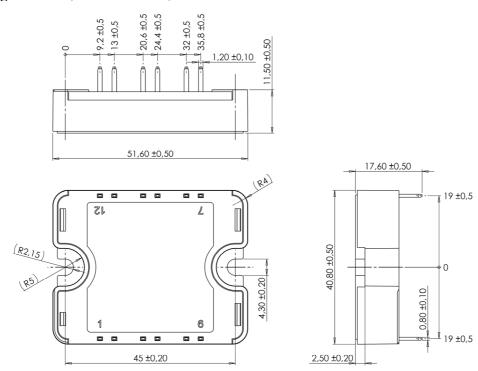
Temperature sensor NTC (see application note APT0406 on www.microsemi.com for more information).

Symbol	Characteristic	Min	Тур	Max	Unit
R ₂₅	Resistance @ 25°C		50		kΩ
B 25/85	$T_{25} = 298.15 \text{ K}$		3952		K

$$R_T = \frac{R_{25}}{\exp \left[B_{25/85} \left(\frac{1}{T_{25}} - \frac{1}{T} \right) \right]} \quad \text{T: Thermistor temperature}$$

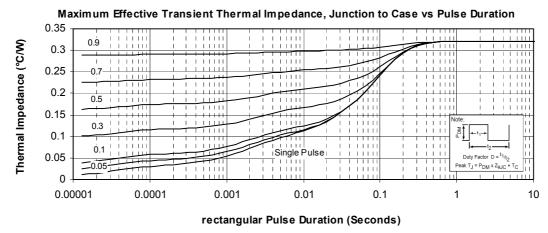
$$R_T: \text{ Thermistor value at T}$$

SP1 Package outline (dimensions in mm)

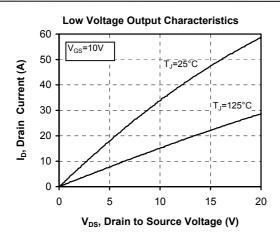


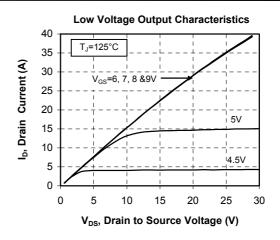
See application note 1904 - Mounting Instructions for SP1 Power Modules on www.microsemi.com

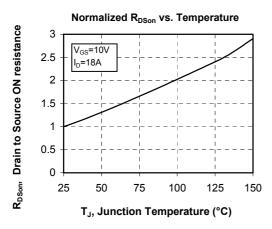
Typical Mosfet Performance Curve

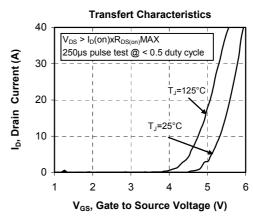


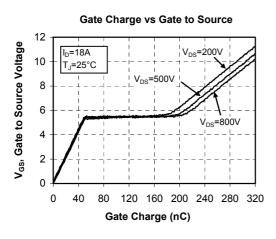


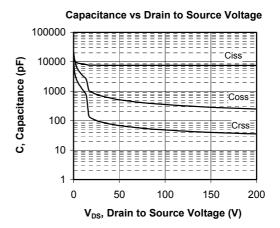






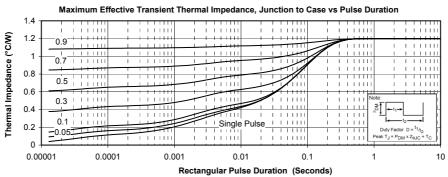


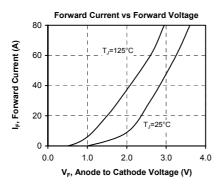


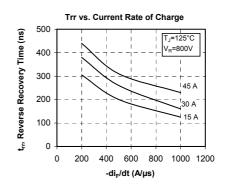


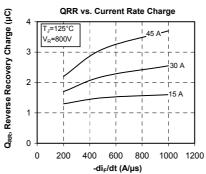


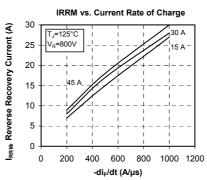
Typical Diode Performance Curve

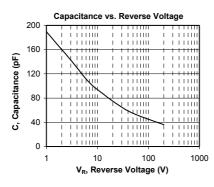


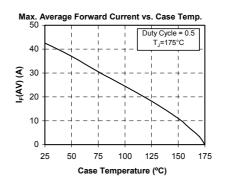












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